

Title (en)

Etching of silicon nitride by anhydrous halogen gas

Title (de)

Ätzen von Siliziumnitrid mittels wasserfreiem Halogengas

Title (fr)

Attaque chimique du nitrure de silicium par un gaz halogène anhydre

Publication

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Application

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Priority

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Abstract (en)

The present invention discloses a method for removing silicon nitride from a substrate by etching, characterised in that it comprises the following steps: bringing the surface temperature of said substrate to at least 125 DEG C, and contacting said substrate with anhydrous hydrogen halogenide, and characterised in that the silicon nitride etching rate is at least 20 nm/min. <IMAGE>

IPC 1-7

H01L 21/311

IPC 8 full level

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CPC (source: EP US)

H01L 21/31116 (2013.01 - EP US); **H01L 21/0217** (2013.01 - EP)

Citation (search report)

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